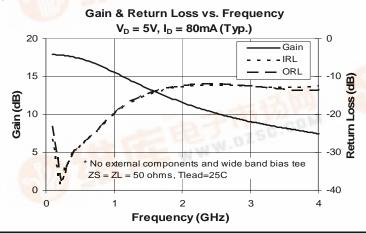


Sirenza Microdevices' SGC-6386Z is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 5V supply, the SGC-6386Z does not require a drop resistor as compared to typical Darlington amplifiers. The SGC-6386Z product is designed for high linearity 5V gain block applications that require small size and minimal external components. It is internally matched to 50 ohms.

The matte tin finish on Sirenza's lead-free "Z" package is applied using a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. The package body is manufactured with green molding compounds that contain no antimony trioxide or halogenated fire retardants.



#### **Preliminary Information**

**SGC-6386Z** 



# 50-4000 MHz Silicon Germanium Cascadable Gain Block



#### **Product Features**

- Single Fixed 5V Supply
- Supply Drop Resistor not required
- Patented Self Bias Circuitry
- P1dB = 18.3 dBm at 1950 MHz
- IP3 = 34.3 dBm at 1950 MHz
- Robust 1000V ESD, Class 1C HBM

### **Applications**

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Typical perfor	mance with appropriate application circuit	WWW.DZ				
Symbol	Parameters	Units	Frequency	Min.	Тур.	Max.
G	Small Signal Gain	dB	850 MHz		16.3	
	Leg. Cur		1950 MHz		11.9	
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm	850 MHz		19.3	
¹ 1dB	Output Fower at 10B Compression	dDill	1950 MHz		18.3	
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm	850 MHz		35.6	
OIF 3	Output Third Order Intercept Point	UDIII	1950 MHz	-15	34.3	
IRL	Input Return Loss	dB	1950 MHz	起了	18.0	
ORL	Output Return Loss	dB	1950 MHz	Mala	17.0	
NF	Noise Figure	dB	1930 MHz		4.2	
V <sub>D</sub>	Device Operating Voltage	V			5.0	
I <sub>D</sub>	Device Operating Current	mA			80	
Rth, j-l	Thermal Resistance (junction to lead)	°C/W			106	

**Test Conditions:** 

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roomfield, CO 80021

 $V_{\rm D} = 5.0 V$ 

 $I_D = 80 \text{mA Typ.}$ 

OIP<sub>3</sub> Tone Spacing = 1MHz

 $T_L = 25^{\circ}C$ 

 $Z_S = Z_L = 50 \text{ Ohms}$ 

Pout per tone = 0 dBm

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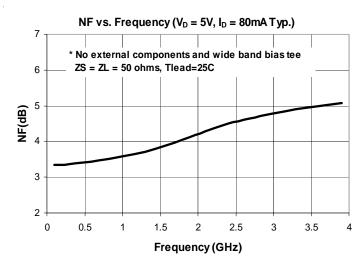




	Typical RF Performance at Key Operating Frequencies (Application Circuit)							
			Frequency (MHz)					
Symbol	Parameter	Unit	100 - 1000MHz App. Circuit			1000 - 2200MHz App. Circuit		
			100	500	850	1000	1950	2200
G	S Small Signal Gain		17.5	17.3	16.2	15.1	11.9	11.1
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm	35.8	36.2	35.6	34.9	34.3	33.6
P <sub>1dB</sub>	P <sub>1dB</sub> Output Power at 1dB Compression		19.4	19.7	19.3	18.9	18.3	18.0
IRL	Input Return Loss	dB	10.0	35.0	21.0	12.0	18.0	16.0
ORL	ORL Output Return Loss  S <sub>12</sub> Reverse Isolation  NF Noise Figure		12.0	20.0	22.0	15.0	17.0	15.0
S <sub>12</sub>			21.0	21.0	21.0	21.0	19.0	18.0
NF			3.1	3.3	3.4	3.5	4.2	4.3

Test Conditions:  $V_D = 5V$ 

V<sub>D</sub> = 5V T₁ = 25°C  $I_D = 80$ mA Typ.  $Z_S = Z_L = 50$  Ohms OIP<sub>3</sub> Tone Spacing = 1MHz, Pout per tone = 0 dBm



Absolute Maximum Ratings				
Parameter	Absolute Limit 120 mA			
Max Device Current (I <sub>CE</sub> )				
Max Device Voltage (V <sub>CE</sub> )	6.5 V			
Max. RF Input Power* (See Note)	+18 dBm			
Max. Junction Temp. (T <sub>J</sub> )	+150°C			
Operating Temp. Range (T <sub>L</sub> )	-40°C to +85°C			
Max. Storage Temp.	+150°C			

\*Note: Load condition,  $Z_L = 50$  Ohms

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:  $I_DV_D<(T_J-T_L)\:/\:R_{TH},\:j\text{-}I \qquad T_L\text{=}T_{LEAD}$ 

	ld v	s. Vd V	/s. Te	mperatu	ıre		
						1/2	
							$\dashv$
				·J.			
	T=-40C						
		and sixe	and the second				
0	10			0	1.0	5.0	
.0	1.0	2.0			4.0	5.0	6.0
		T=-40C T=25C T=85C	T=25C T=85C	T=25C T=85C	T=25C — T=85C	T=25C T=85C .0 1.0 2.0 3.0 4.0	T=25C T=85C  0 1.0 2.0 3.0 4.0 5.0

Reliability & Qualification Information				
Parameter	Rating			
ESD Rating - Human Body Model (HBM)	Class 1C			
Moisture Sensitivity Level	MSL 1			

This product qualification report can be downloaded at www.sirenza.com

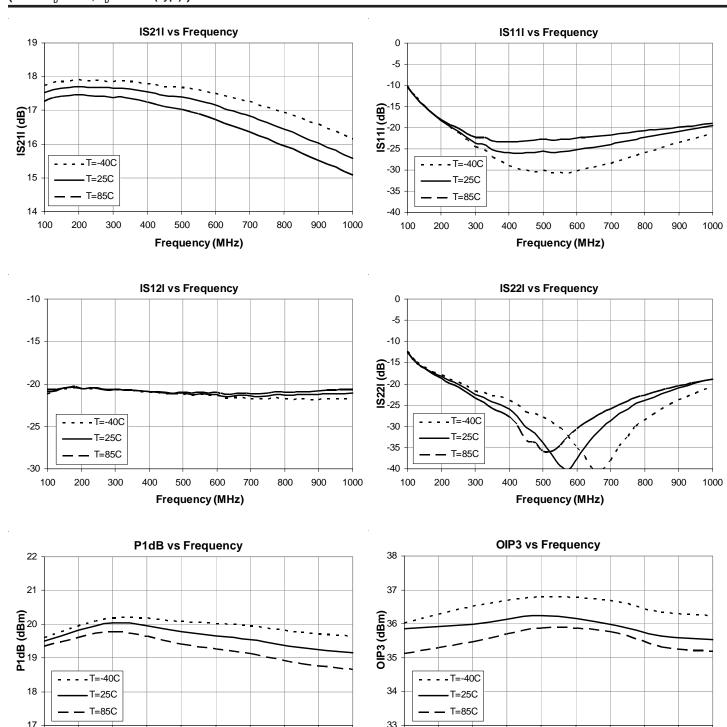


#### **Caution: ESD sensitive**

Appropriate precautions in handling, packaging and testing devices must be observed.



## Typical RF Performance, 100-1000 MHz Application Circuit ( Bias: $V_D = 5.0 \text{ V}$ , $I_D = 80 \text{ mA (Typ.)}$ )



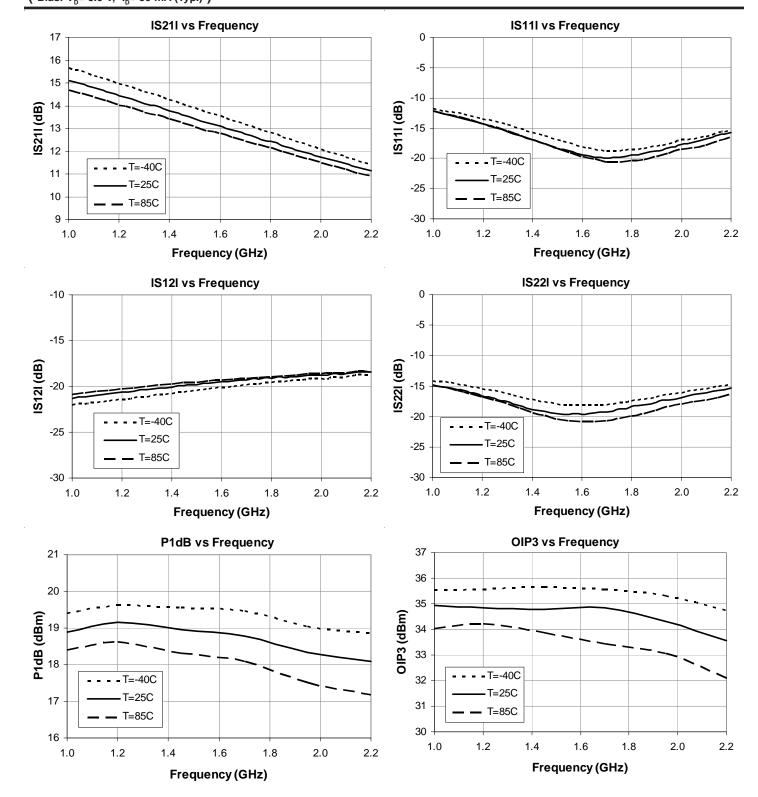
Frequency (MHz)

Phone: (800) SMI-MMIC 

Frequency (MHz)

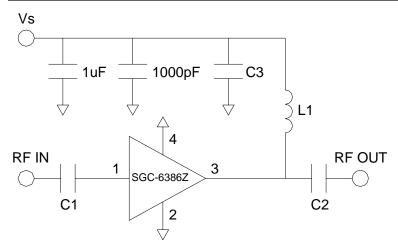


Typical RF Performance, 1000-2200 MHz Application Circuit ( Bias:  $V_D = 5.0 \text{ V}$ ,  $I_D = 80 \text{ mA}$  (Typ.) )

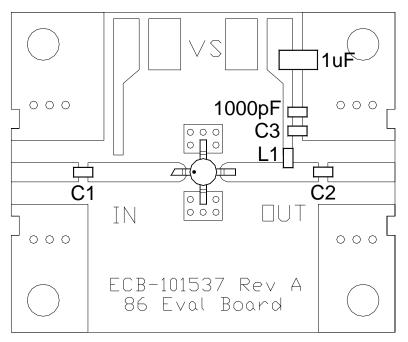


Phone: (800) SMI-MMIC





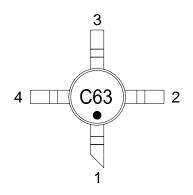
Applicat	Application Circuit Element Values					
Reference Designator	100-1000MHz	1000-2200MHz				
C1	1000pF	6.8pF				
C2	100pF	6.8pF				
C3	100pF	6.8pF				
L1	100nH	39nH				



#### **Mounting Instructions**

- 1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
- We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

#### **Part Identification Marking & Pinout**



	Pin #	Function	Description
	1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation
	<b>2,4</b> GND		Connection to ground. Use via holes as close to the device ground leads as possible to reduce ground inductance and achieve optimum RF performance
3 RF OUT / DCBIAS			RF output and bias pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.

Part	Package /	Reel Size	Devices /
Number	Lead Composition		Reel
SGC-6386Z	Lead Free, RoHS Compliant	13"	3000

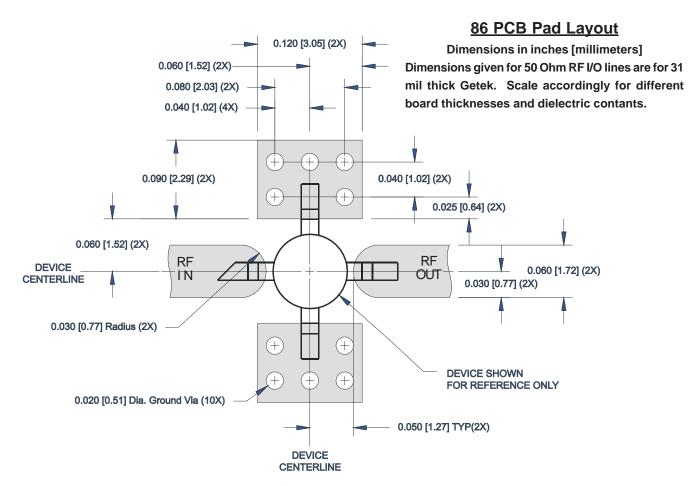
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http://www.sirenza.com

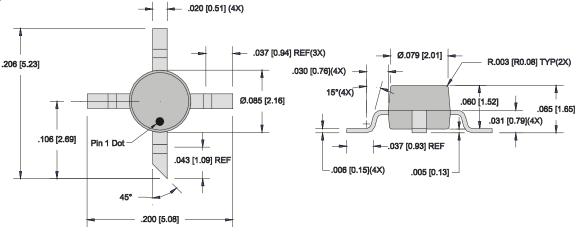




# 86 Nominal Package Dimensions

Dimensions in inches [millimeters]

A link to the 86 package outline drawing with full dimensions and tolerances may be found on the product web page at www.sirenza.com.



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